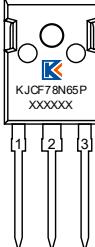


## Product Information

$V_{DS}$	$I_D$	$R_{DS(ON)}$ , max	Pin Assignment and Marking					
650 V	43 A	78 mΩ @ $V_{GS}=10$ V	 TO-247-3L					
<b>Features</b>								
<ul style="list-style-type: none"> <li>• Through-hole package</li> <li>• Super Junction technology</li> <li>• Much lower FOM for fast switching efficiency</li> </ul>								
<b>Applications</b>								
<ul style="list-style-type: none"> <li>• Charger</li> <li>• Solar Inverter System</li> <li>• LED/LCD/PDP TV and monitor Lighting</li> </ul>								
<b>100% Avalanche Tested</b>			  	G: Gate D: Drain S: Source				

## Package and Ordering Information

Part number	Package	Packaging	Quantity (pcs)	Reel size	Tape width
KJCF78N65P	TO-247-3L	<input type="checkbox"/> Tape & Reel	N/A	N/A	N/A
		<input checked="" type="checkbox"/> Tube	30	N/A	N/A

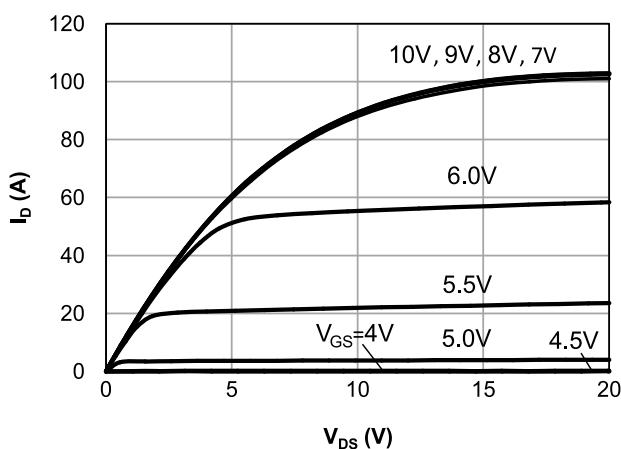
## Absolute Maximum Ratings ( $T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Conditions	Values	Unit
Drain-Source Voltage	$V_{DS}$	$T_C=25^\circ\text{C}$	650	V
Gate-Source Voltage	$V_{GS}$	$T_C=25^\circ\text{C}$	$\pm 30$	V
Drain Current (DC)	$I_D$	$T_C=25^\circ\text{C}, V_{GS}=10$ V	43	A
		$T_C=100^\circ\text{C}, V_{GS}=10$ V	27.3	A
Drain Current (Pulsed)	$I_{DM}$	$T_C=25^\circ\text{C}, V_{GS}=10$ V	172	A
Total Power Dissipation	$P_{tot}$	$T_C=25^\circ\text{C}$	47	W
Single Pulsed Avalanche Energy	$E_{AS}$	$L=60$ mH, $R_g=30$ Ω	3434	mJ
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$		-55–150	°C
Thermal Resistance, Junction to Ambient	$R_{thJA}$		45	°C/W
Thermal Resistance, Junction to Case	$R_{thJC}$		2.65	°C/W

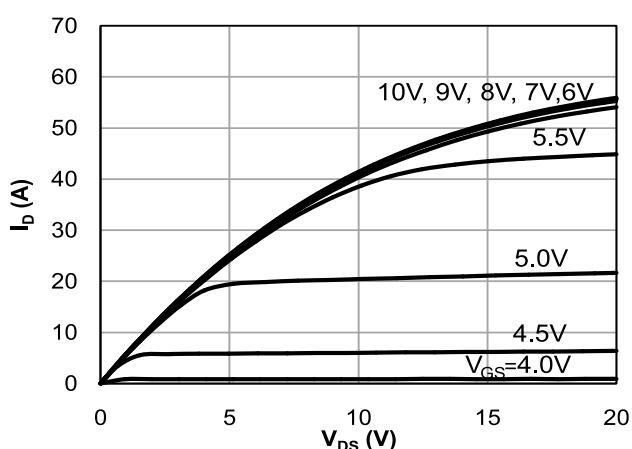
**Electrical Characteristics** ( $T_J=25^\circ\text{C}$  unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
<b>Static Characteristics</b>						
Drain-Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}}=0 \text{ V}, I_{\text{DS}}=250 \mu\text{A}$	650	-	-	V
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{DS}}=250 \mu\text{A}$	3	-	4	V
Zero Gate Voltage Source Current	$I_{\text{DSS}}$	$V_{\text{GS}}=0 \text{ V}, V_{\text{DS}}=650 \text{ V}, T_c=25^\circ\text{C}$	-	-	1	$\mu\text{A}$
		$V_{\text{GS}}=0 \text{ V}, V_{\text{DS}}=650 \text{ V}, T_c=100^\circ\text{C}$	-	50	-	$\mu\text{A}$
Gate Leakage Current	$I_{\text{GSS}}$	$V_{\text{DS}}=0 \text{ V}, V_{\text{GS}}=\pm 30 \text{ V}$	-	-	$\pm 100$	nA
Drain-Source On-State Resistance	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}}=10 \text{ V}, I_{\text{D}}=21.5 \text{ A}, T_c=25^\circ\text{C}$	-	66	78	$\text{m}\Omega$
		$V_{\text{GS}}=10 \text{ V}, I_{\text{D}}=21.5 \text{ A}, T_c=100^\circ\text{C}$	-	175	-	$\text{m}\Omega$
<b>Dynamic Characteristics</b>						
Input Capacitance	$C_{\text{iss}}$	$V_{\text{DS}}=100 \text{ V}, V_{\text{GS}}=0 \text{ V}, \text{Frequency}=1 \text{ MHz}$	-	4200	-	pF
Output Capacitance	$C_{\text{oss}}$		-	135	-	
Reverse Transfer Capacitance	$C_{\text{rss}}$		-	1.9	-	
Turn-on Delay Time	$t_{\text{d}(\text{on})}$	$V_{\text{DS}}=400 \text{ V}, V_{\text{GS}}=10 \text{ V}, R_{\text{G}}=27 \Omega, I_{\text{D}}=21.5 \text{ A}$	-	76	-	ns
Turn-on Rise Time	$t_{\text{r}}$		-	70	-	
Turn-off Delay Time	$t_{\text{d}(\text{off})}$		-	365	-	
Turn-off Fall Time	$t_{\text{f}}$		-	68	-	
Total Gate Charge	$Q_{\text{g}}$	$V_{\text{DS}}=480 \text{ V}, V_{\text{GS}}=10 \text{ V}, I_{\text{DS}}=21.5 \text{ A}$	-	112	-	nC
Gate-Source Charge	$Q_{\text{gs}}$		-	28	-	
Gate-Drain Charge	$Q_{\text{gd}}$		-	44	-	
Gate resistance	$R_{\text{G}}$	$f=1 \text{ MHz}$				
<b>Body Diode Characteristics</b>						
Diode Forward Voltage [2]	$V_{\text{SD}}$	$V_{\text{GS}}=0 \text{ V}, I_{\text{SD}}=21.5 \text{ A}$	-	0.85	1.1	V
Reverse Recovery Time	$t_{\text{rr}}$	$V_{\text{GS}}=0 \text{ V}, I_{\text{DS}}=21.5 \text{ A}, dI_{\text{SD}}/dt=100 \text{ A}/\mu\text{s}$	-	488	-	ns
Reverse Recovery Charge	$Q_{\text{rr}}$		-	8.8	-	$\mu\text{C}$

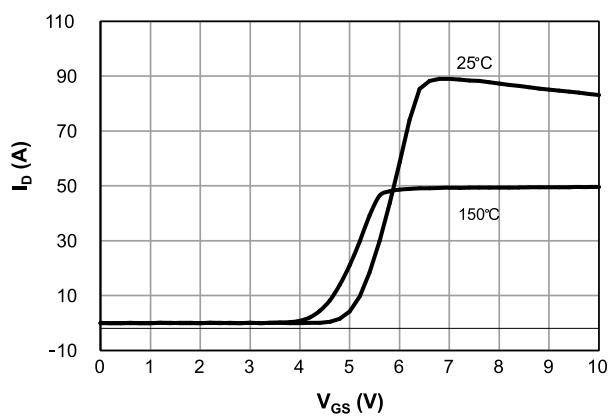
## Typical Characteristics



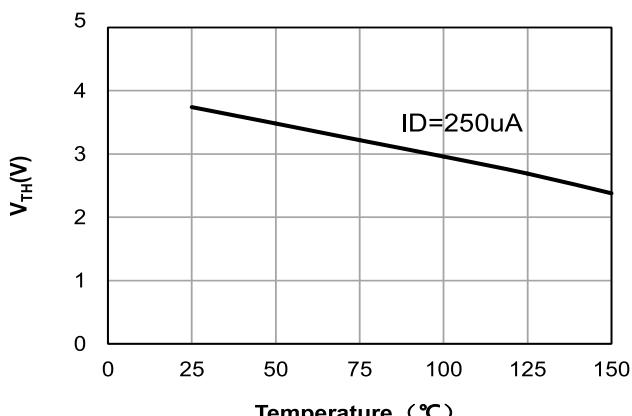
**Figure 1. Output Characteristics ( $T_j=25^\circ\text{C}$ )**



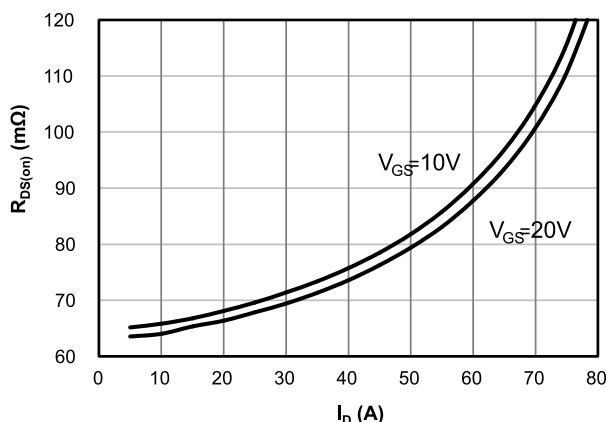
**Figure 2. Output Characteristics ( $T_j=150^\circ\text{C}$ )**



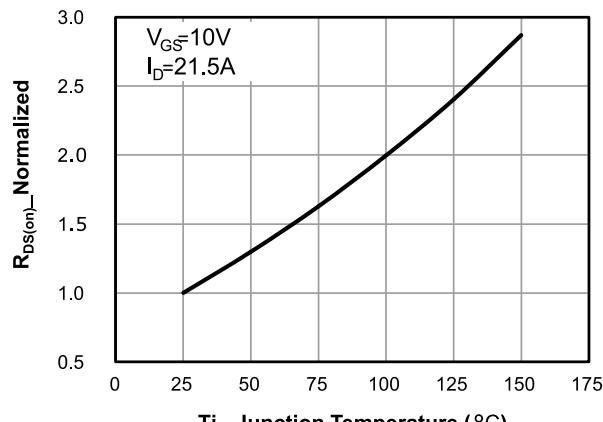
**Figure 3. Transfer Characteristics**



**Figure 4.  $V_{TH}$  Vs  $T_j$  Temperature Characteristics**

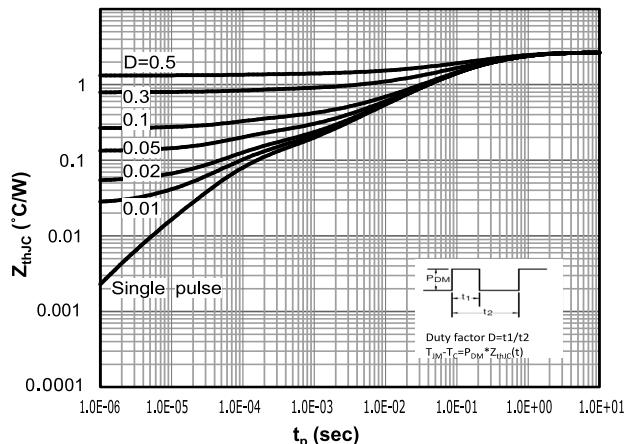


**Figure 5.  $R_{DS(on)}$  vs  $I_{DS}$  Characteristics( $T_c=25^\circ\text{C}$ )**

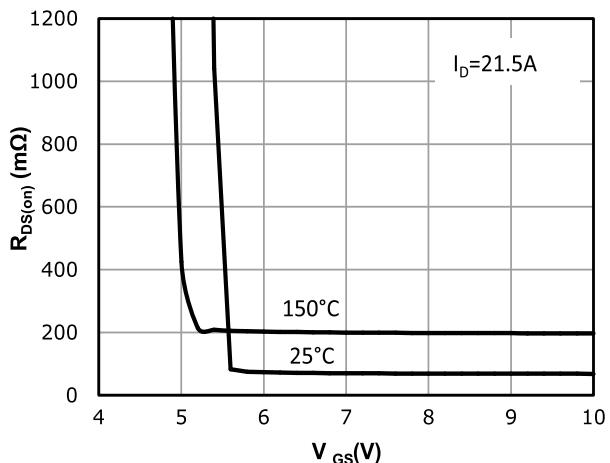


**Figure 6.  $R_{DS(on)}$  vs Temperature**

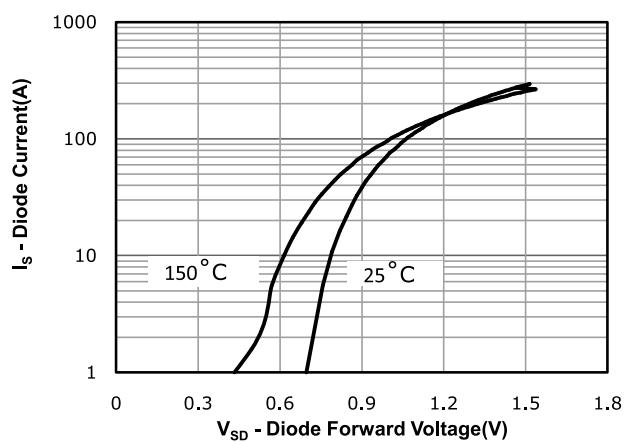
## Typical Characteristics (cont.)



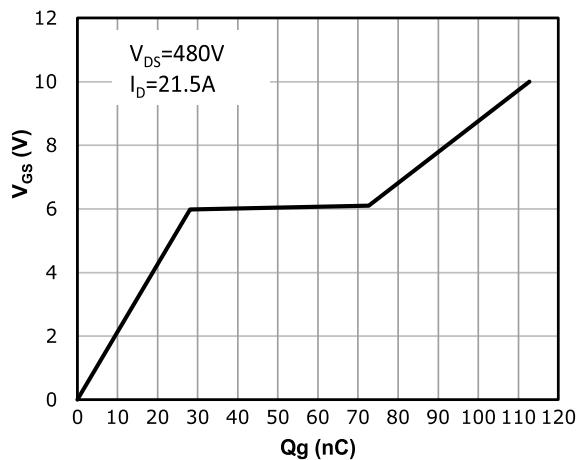
**Figure 7. Max. Transient Thermal Impedance**



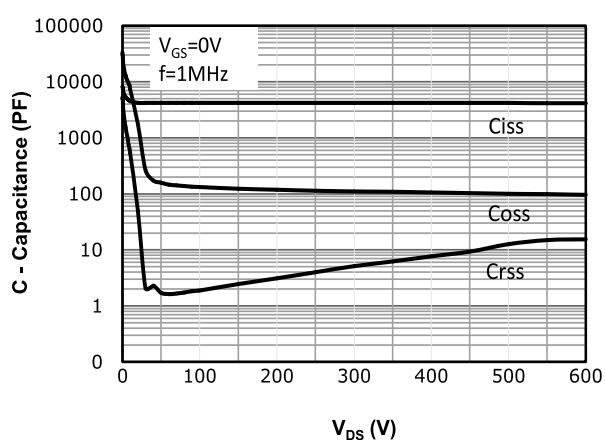
**Figure 8.  $R_{DS(on)}$  vs Gate Voltage**



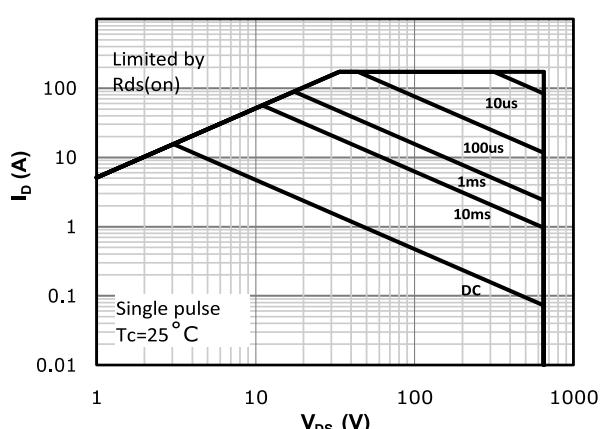
**Figure 9. Body-diode Forward Characteristics**



**Figure 10. Gate Charge Characteristics**



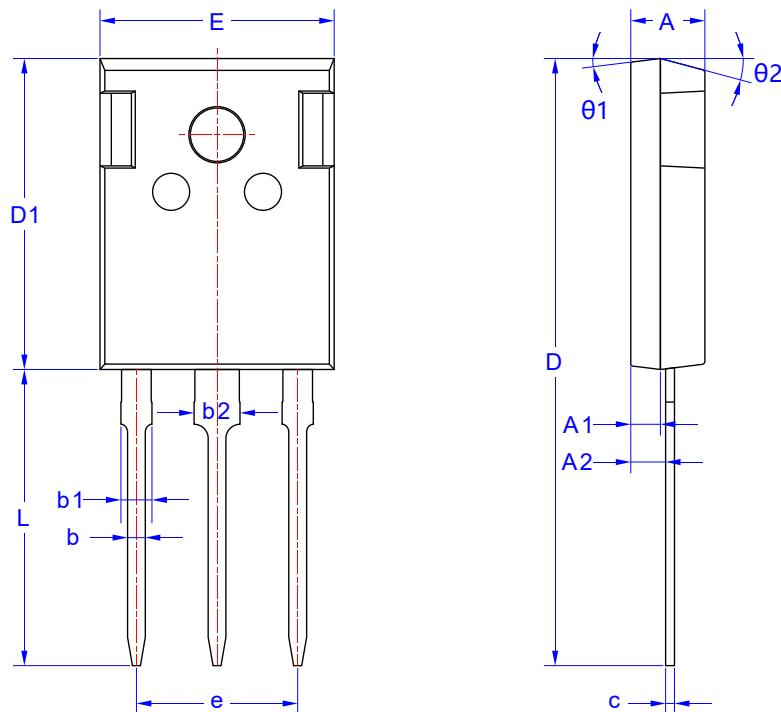
**Figure 11. Capacitance**



**Figure 12. Safe Operating Area**

**Package Dimensions**

TO-247-3L



Symbol	Dimensions in Millimeters		
	MIN	NOM	MAX
A	4.90	5.00	5.10
A1	1.90	2.00	2.10
A2	2.25	2.35	2.45
b		1.20	
b1		2.10	
b2		3.10	
c		0.60	
D	40.00	41.00	42.00
D1	20.80	21.00	21.20
E	15.60	15.80	16.00
e		10.88	
L	19.80	20.00	20.20
θ1		7°	
θ2		15°	